



STSJ25NF3LL

N-CHANNEL 30V - 0.0085 Ω - 25A PowerSO-8™ LOW GATE CHARGE STripFET™ II POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STSJ25NF3LL	30 V	<0.0105 Ω	25 A

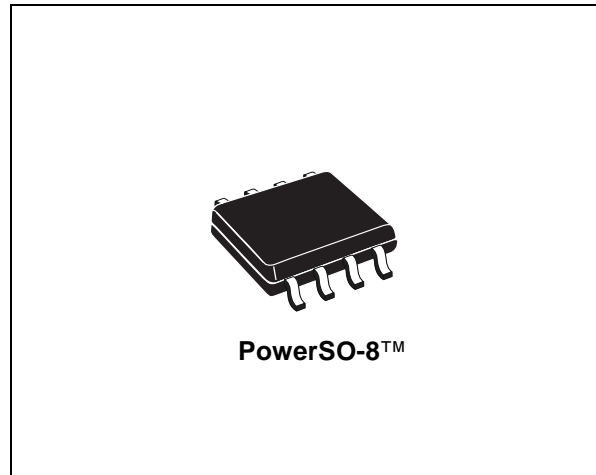
- TYPICAL R_{DS(on)} = 0.0085 Ω @ 10V
- TYPICAL Q_g = 24 nC @ 4.5 V
- CONDUCTION LOSSES REDUCED
- SWITCHING LOSSES REDUCED
- IMPROVED JUNCTION-CASE THERMAL RESISTANCE

DESCRIPTION

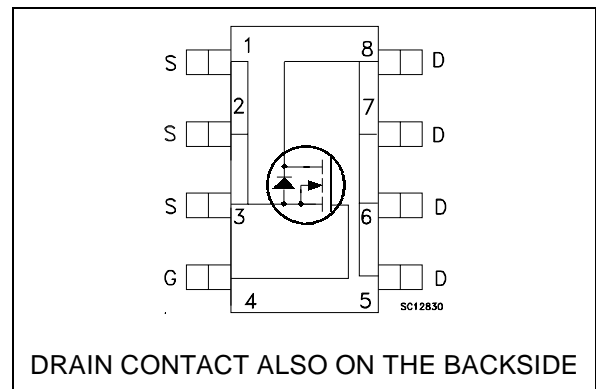
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. This silicon, housed in thermally improved SO-8™ package, exhibits optimal on-resistance versus gate charge trade-off plus lower R_{thj-c}.

APPLICATIONS

- SPECIFICALLY DESIGNED AND OPTIMISED FOR HIGH EFFICIENCY CPU CORE DC/DC CONVERTERS FOR MOBILE PC_S



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	30	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	30	V
V _{GS}	Gate- source Voltage	± 16	V
I _D	Drain Current (continuous) at T _C = 25°C (*)	25	A
I _D	Drain Current (continuous) at T _C = 25°C (#)	12	A
I _D	Drain Current (continuous) at T _C = 100°C	16	A
I _{DM} (●)	Drain Current (pulsed)	100	A
P _{tot}	Total Dissipation at T _C = 25°C	70	W
	Total Dissipation at T _C = 25°C (#)	3	W

(●) Pulse width limited by safe operating area.

(*) Value limited by wires bonding

STSJ25NF3LL

THERMAL DATA

Rthj-c	Thermal Resistance Junction-case	Max	1.8	°C/W
Rthj-amb	(*)Thermal Resistance Junction-ambient	Max	42	°C/W
T _j	Maximum Operating Junction Temperature		150	°C
T _{stg}	Storage Temperature		-55 to 150	°C

(*) When mounted on FR-4 board with 0.5 in² pad of Cu.

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	30			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 16 V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	1			V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 12.5 A V _{GS} = 4.5 V I _D = 12.5 A		0.0085 0.011	0.0105 0.013	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} =15 V I _D = 12.5 A		20		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		1650		pF
C _{oss}	Output Capacitance			540		pF
C _{rss}	Reverse Transfer Capacitance			130		pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 15\text{ V}$ $I_D = 12.5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 1)		23 156		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD}=15\text{V}$ $I_D=25\text{A}$ $V_{GS}=4.5\text{V}$ (see test circuit, Figure 2)		24 8.5 12	33	nC nC nC

SWITCHING OFF

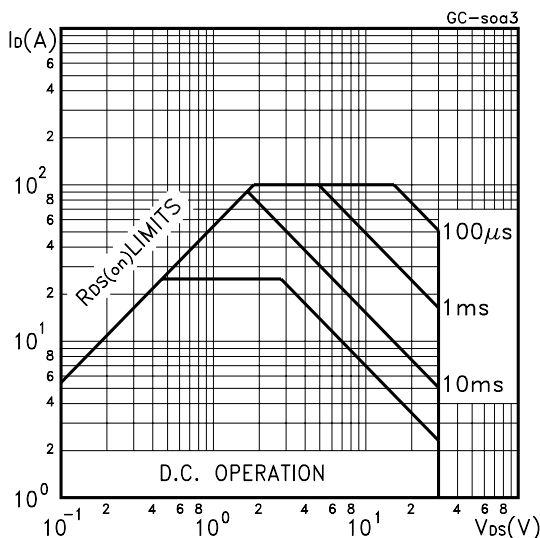
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 15\text{ V}$ $I_D = 12.5\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 3)		27 28		ns ns

SOURCE DRAIN DIODE

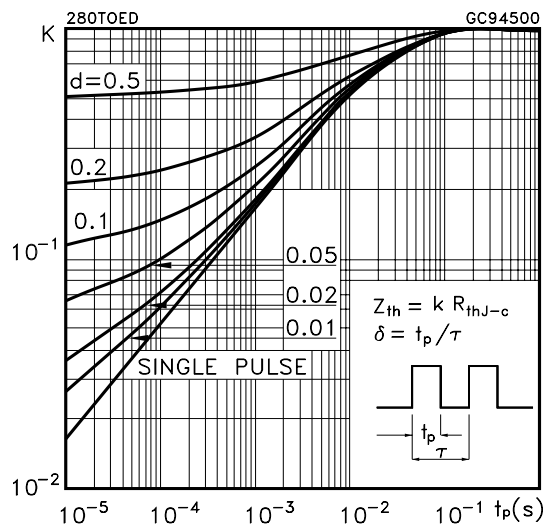
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (\bullet)$	Source-drain Current Source-drain Current (pulsed)				25 100	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 25\text{ A}$ $V_{GS} = 0$			1.2	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 25\text{ A}$ $di/dt = 100\text{A}/\mu\text{s}$ $V_{DD} = 25\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 3)		40 50 2.5		ns nC A

(*)Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
(\bullet)Pulse width limited by safe operating area.

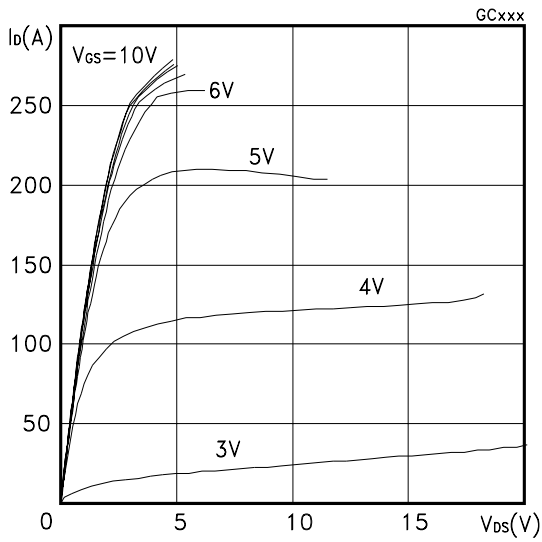
Safe Operating Area



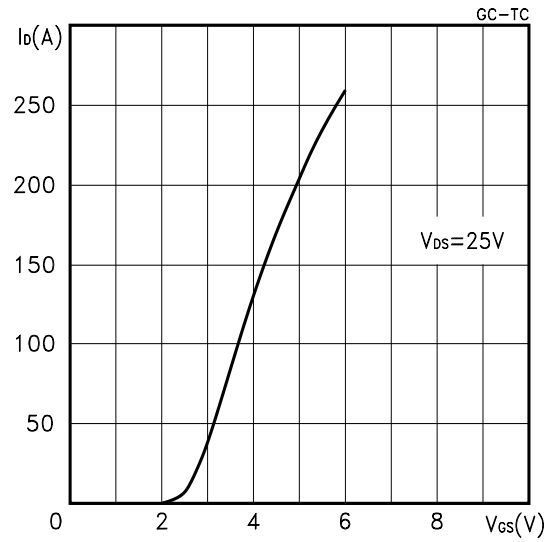
Thermal Impedance



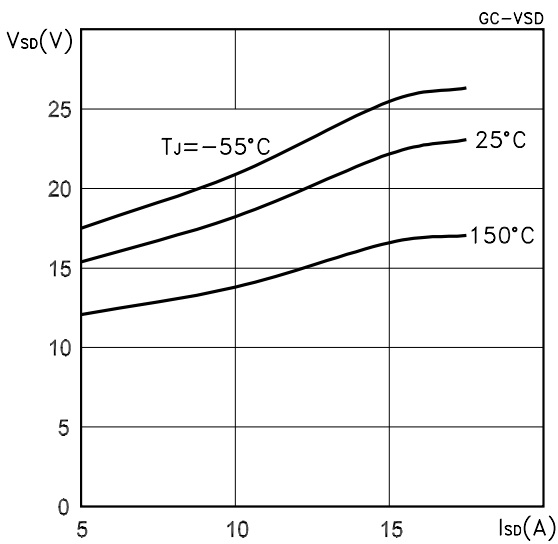
Output Characteristics



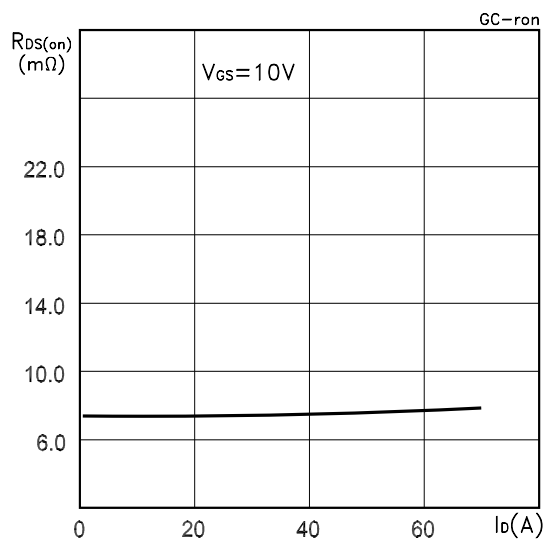
Transfer Characteristics



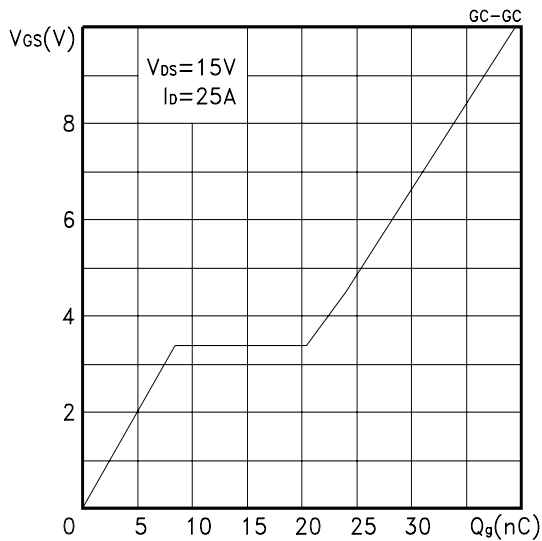
Transconductance



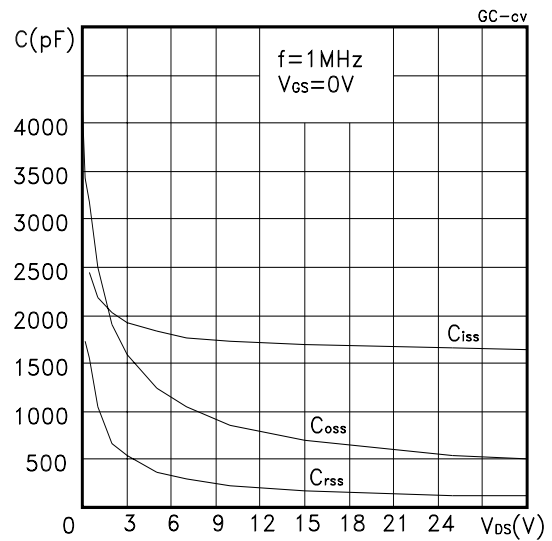
Static Drain-source On Resistance



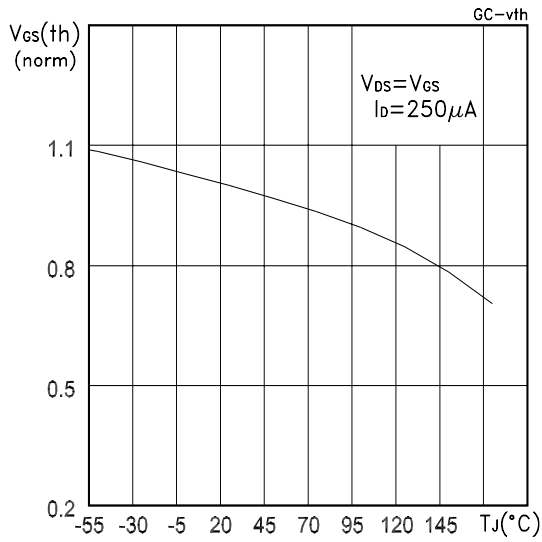
Gate Charge vs Gate-source Voltage



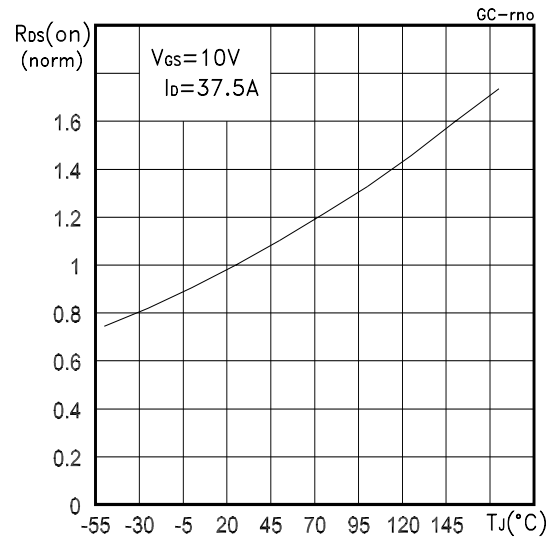
Capacitance Variations



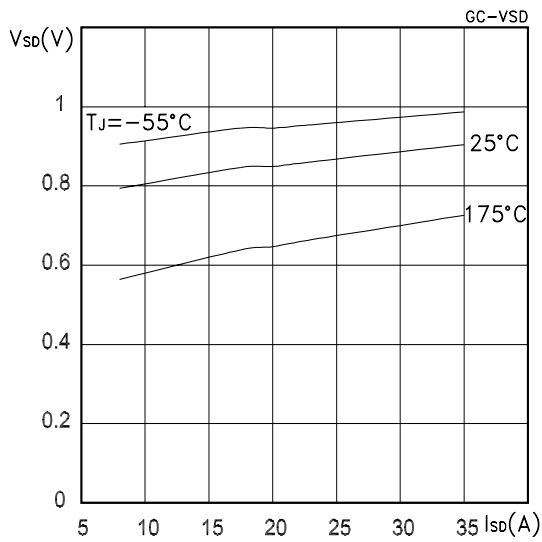
Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage vs Temperature.

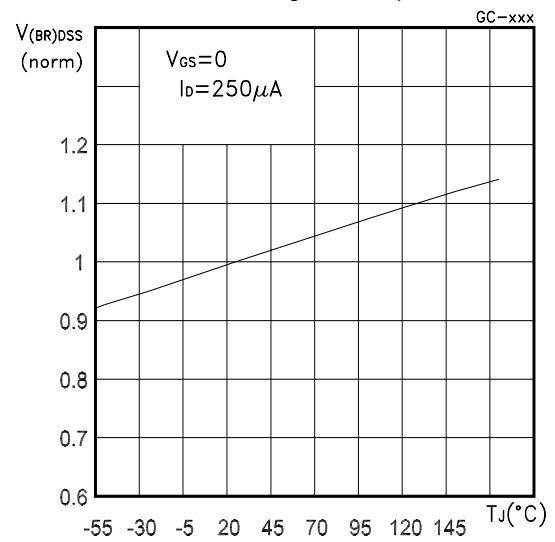


Fig. 1: Switching Times Test Circuits For Resistive Load

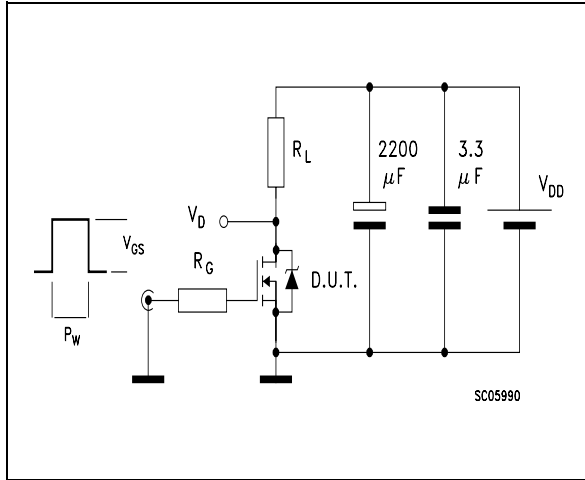


Fig. 2: Gate Charge test Circuit

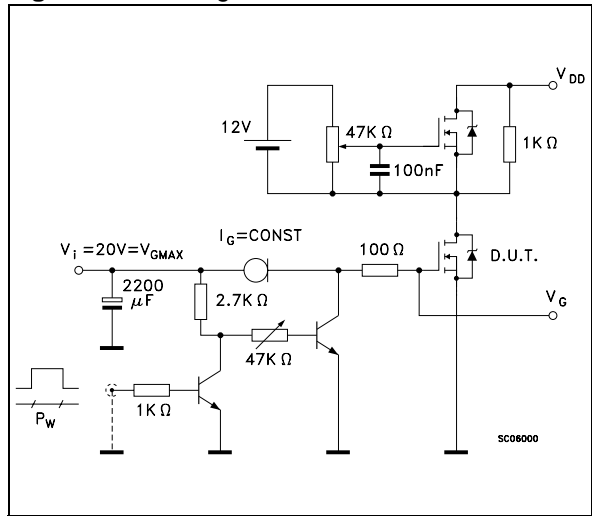
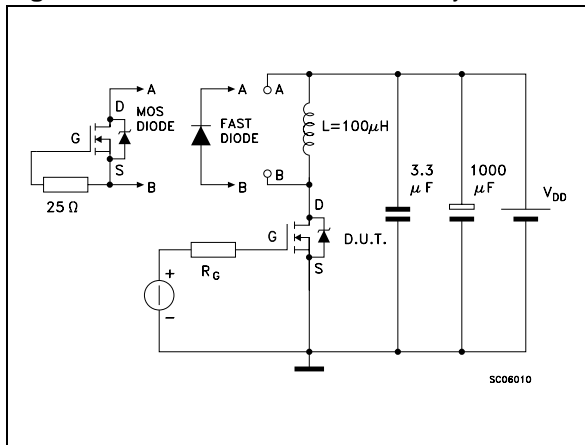
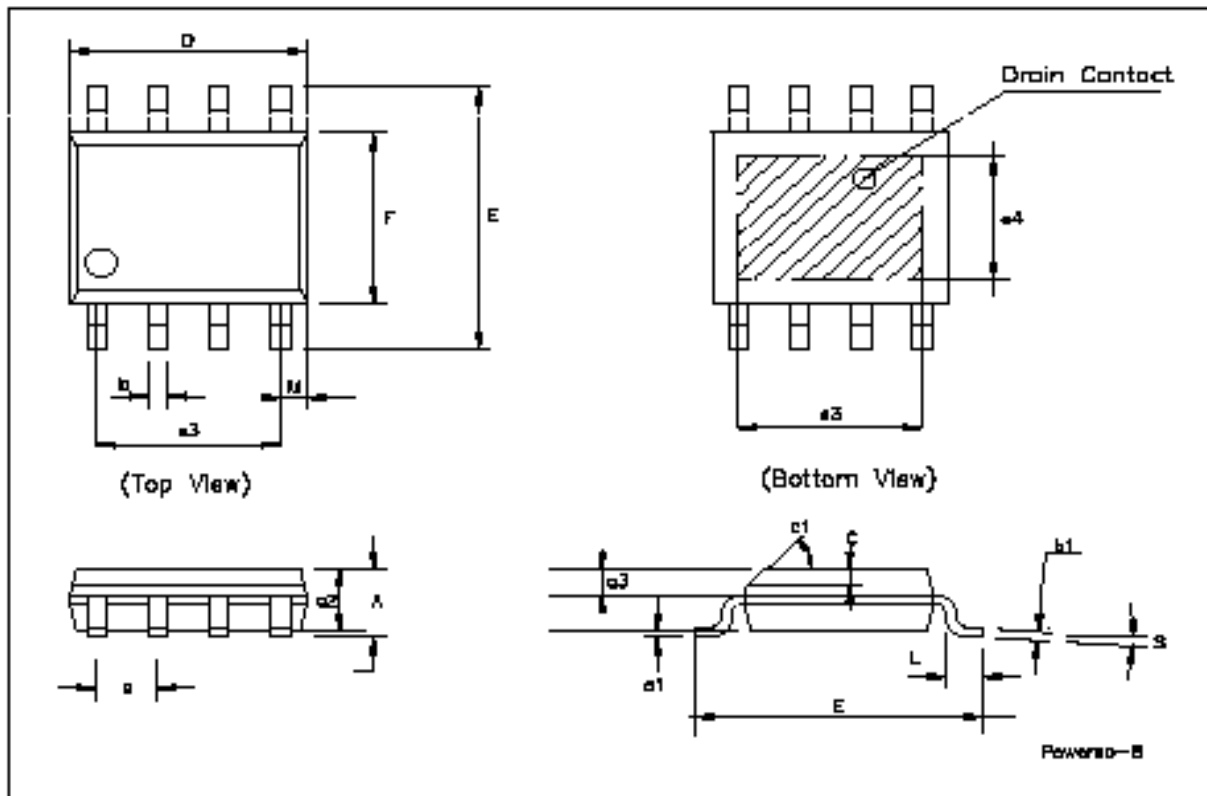


Fig. 3: Test Circuit For Diode Recovery Behaviour



PowerSO-8™ MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45° (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
e4		2.79			0.110	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8° (max.)					



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is registered trademark of STMicroelectronics
All other names are the property of their respective owners.

© 2003 STMicroelectronics - All Rights Reserved

STMicroelectronics GROUP OF COMPANIES

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -
Malaysia - Malta - Morocco -Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

www.st.com